

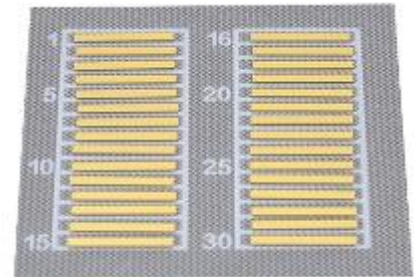
Diode Laser Unmounted Single Emitters and Bars

808nm 100W Unmounted Bar

Semiconductor lasers are the centerpiece of most of today's industrial laser systems. Whether direct material processing or optical pumping of solid-state lasers, fiber lasers or disc lasers, the unmounted single emitters and bars are the key component for the initial conversion of electrical energy into light.

HTOE has been focusing on the semiconductor wafer technology from 1998, delivers the multimode high power at wavelengths between 635 and 1064nm.

- High Power multimode unmounted bars up to 40W CW and 200W QCW output
- Unmounted single emitters up to 2W CW Power
- Available wavelengths include 635nm, 650nm, 808nm, 980nm and 1064nm



Parameters (25°C)

Parameter		Unit	LDAQ1-0808-0100
Optical Parameter	Operation Mode	-	QCW
	Output Power P_o	W	100
	Center Wavelength λ_c	nm	808 ± 5
Geometrical	Fill Factor	-	87%
	Number of Unmounted Single Emitters	-	100
Electrical Parameter	Slope Efficiency E_s	W/A	≥ 1.2
	Threshold Current I_{th}	A	≤ 20
	Operating Current I_f	A	≤ 100
	Operating Voltage V_f	V	≤ 3



Notice

1. Item notice: LDAQ1(item model)-*****(center wavelength)-*****(output power).
2. Data sheet is based on the result of testing under 25 °C ,pulse width 200 μ s, frequency 1-100Hz, maximum duty cycle 2%, and typical application 0.4%.
3. Data sheet is based on the CS package testing.
4. For more information, please contact Hi-Tech Optoelectronics Co., Ltd.

